

Please replace the paragraph beginning on page 12, line 13, with the following rewritten paragraph:

A7
--The procedure of Example 6 was repeated but using the slurry prepared in Example 5, instead of using the slurry prepared in Example 1 (polishing rate is about 1200 Å/min).--

Please replace the paragraph beginning on page 12, line 18, with the following rewritten paragraph:

A8
--A table movement speed and a wafer revolution number were respectively set up to be 500 fpm and 20 rpm, by using a linear type system. Here, the CMP process was performed on the ruthenium film under a polishing pressure of 1.5 psi by using the slurry prepared in Example 1 (polishing rate is about 1000 Å/min).--

Please replace the paragraph beginning on page 12, line 23, with the following rewritten paragraph:

A9
--A table revolution number and a wafer revolution number were respectively set up to be 20 rpm and 80 rpm, by using a rotary type system. Here, the CMP process was performed on the ruthenium film under a polishing pressure of 4 psi by using a slurry for tungsten (SSW2000 slurry of CABOT) (polishing rate is about 10 Å/min).--

Please replace the paragraph beginning on page 13, line 8, with the following rewritten paragraph:

A10
--A table revolution number and a wafer revolution number were respectively set up to be 20 rpm and 80 rpm, by using a rotary type system. Here, the CMP process was performed on the ruthenium film under a polishing pressure of 4 psi by using a slurry for aluminum (EPA5680 slurry of CABOT) (polishing rate is about 300 Å/min).--

In the Claims:

Please cancel claims 14-23, without prejudice or disclaimer.

Please amend claims 1-3 and 6-8, as follows: